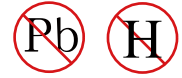




N-Channel Enhancement MOSFET



VDS= 20V, ID= 800mA

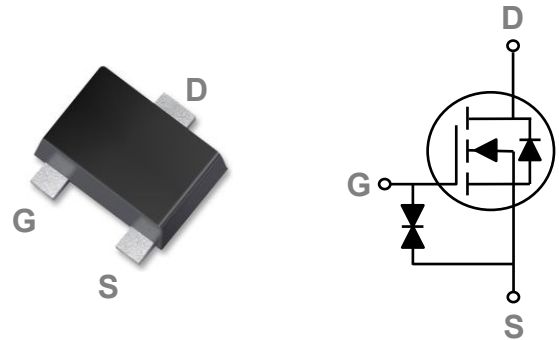
Features

- 20V,800mA, $R_{DS(ON)} = 300m\Omega @ V_{GS} = 4.5V$
- Improved dv/dt capability
- Fast switching
- Green Device Available
- Suit for 1.5V Gate Drive Applications

Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

SOT-723 Pin Configuration



Absolute Maximum Rating $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 8	V
I_D	Drain Current – Continuous ($T_c=25^\circ C$)	800	mA
	Drain Current – Continuous ($T_c=100^\circ C$)	510	mA
I_{DM}	Drain Current – Pulsed ¹	3.2	A
P_D	Power Dissipation ($T_c=25^\circ C$)	450	mW
	Power Dissipation – Derate above $25^\circ C$	3.6	mW/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	280	$^\circ C / W$

DEVICE CHARACTERISTICS

YSE2320XUC

Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	-0.01	---	$V/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=20V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=16V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 8V, V_{DS}=0V$	---	---	± 20	μA

On Characteristics

$R_{DS(ON)}$	Static Drain-source On-Resistance ²	$V_{GS}=4.5V, I_D=0.5A$	---	200	300	$m\Omega$
		$V_{GS}=2.5V, I_D=0.4A$	---	300	450	$m\Omega$
		$V_{GS}=1.8V, I_D=0.2A$	---	500	700	$m\Omega$
		$V_{GS}=1.5V, I_D=0.1A$	---	800	1200	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	0.3	0.5	0.85	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3	---	$mV/^\circ\text{C}$

Dynamic and Switching Characteristics

Q_g	Total Gate Charge ^{2,3}	$V_{DS}=10V, V_{GS}=4.5V, I_D=0.5A$	---	1	2	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	0.26	0.5	
Q_{gd}	Gate-Drain Charge ^{2,3}		---	0.2	0.4	
$T_{d(on)}$	Turn-On Delay Time ^{2,3}	$V_{DD}=10V, V_{GS}=4.5V, R_G=10\Omega, I_D=0.5A$	---	5	10	ns
T_r	Rise Time ^{2,3}		---	3.5	7	
$T_{d(off)}$	Turn-Off Delay Time ^{2,3}		---	14	28	
T_f	Fall Time ^{2,3}		---	6	12	
C_{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V, f=1\text{MHz}$	---	38.2	75	pF
C_{oss}	Output Capacitance		---	14.4	28	
C_{rss}	Reverse Transfer Capacitance		---	6	12	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	0.8	A
I_{SM}	Pulsed Source Current ²		---	---	1.6	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=0.2A, T_J=25^\circ\text{C}$	---	---	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

DEVICE CHARACTERISTICS

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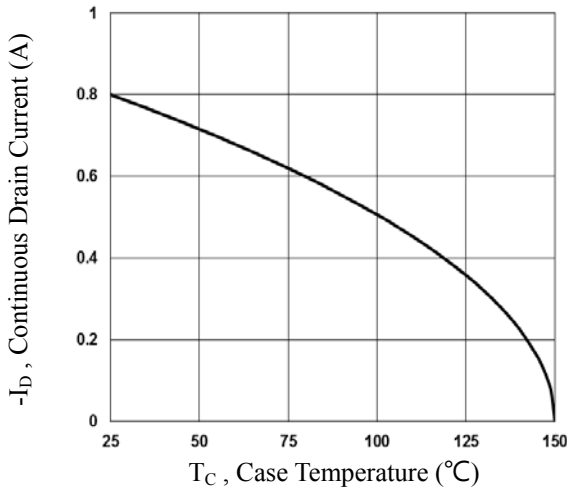


Fig.1 Continuous Drain Current vs. T_C

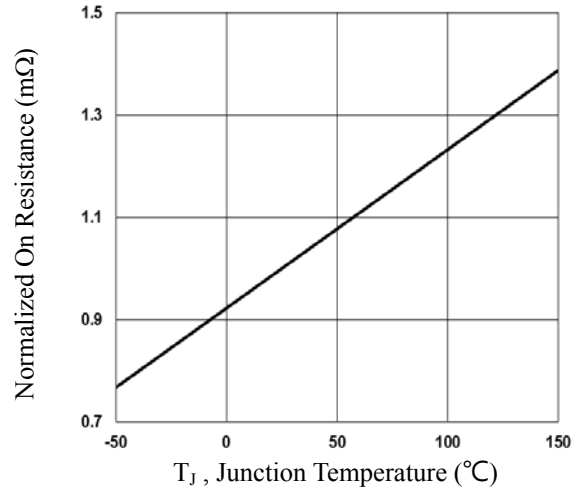


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

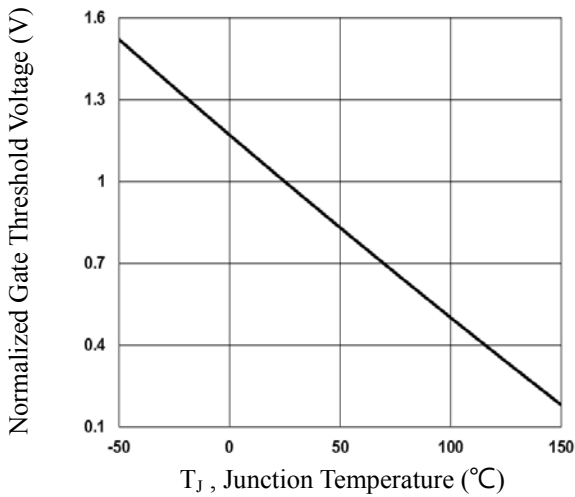


Fig.3 Normalized V_{th} vs. T_J

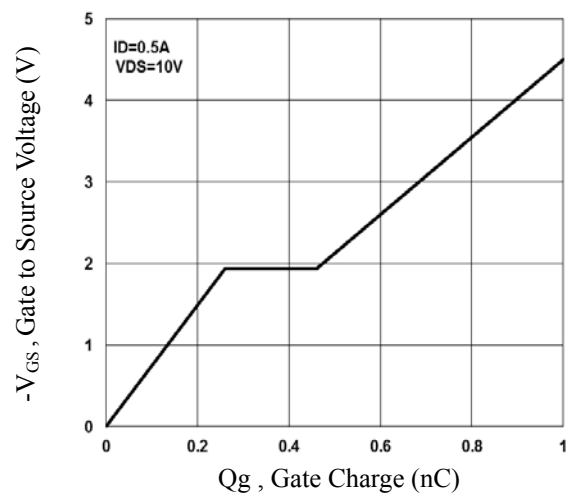


Fig.4 Gate Charge Waveform

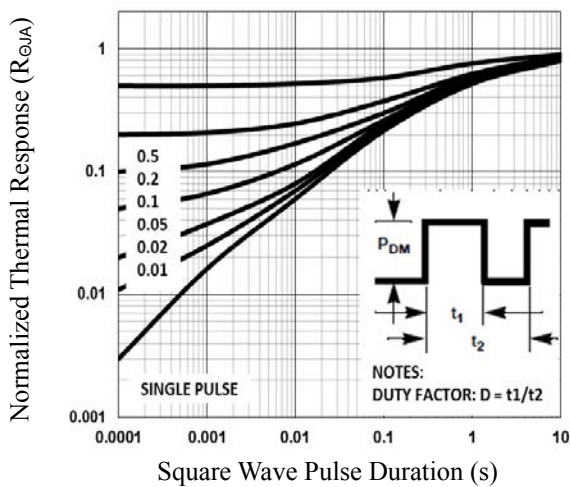


Fig.5 Normalized Transient Response

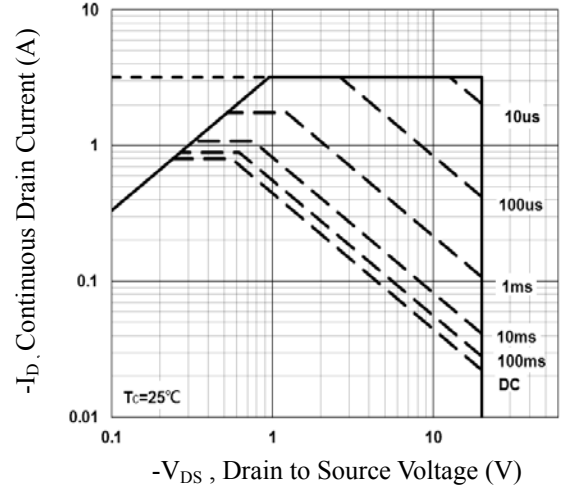


Fig.6 Maximum Safe Operation Area

DEVICE CHARACTERISTICS

YSE2320XUC

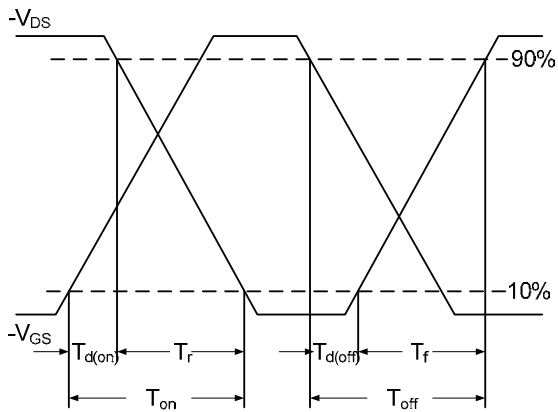


Fig.7 Switching Time Waveform

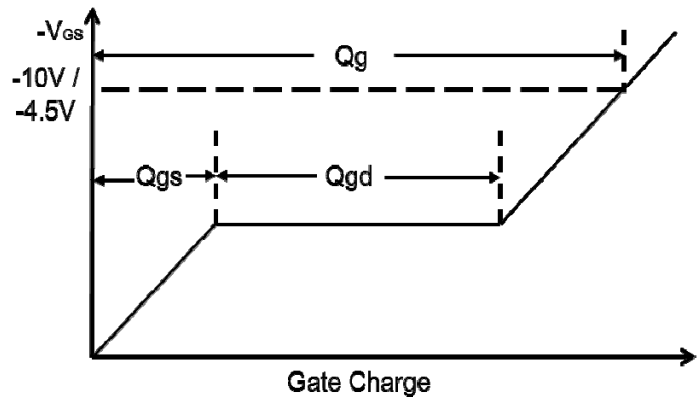
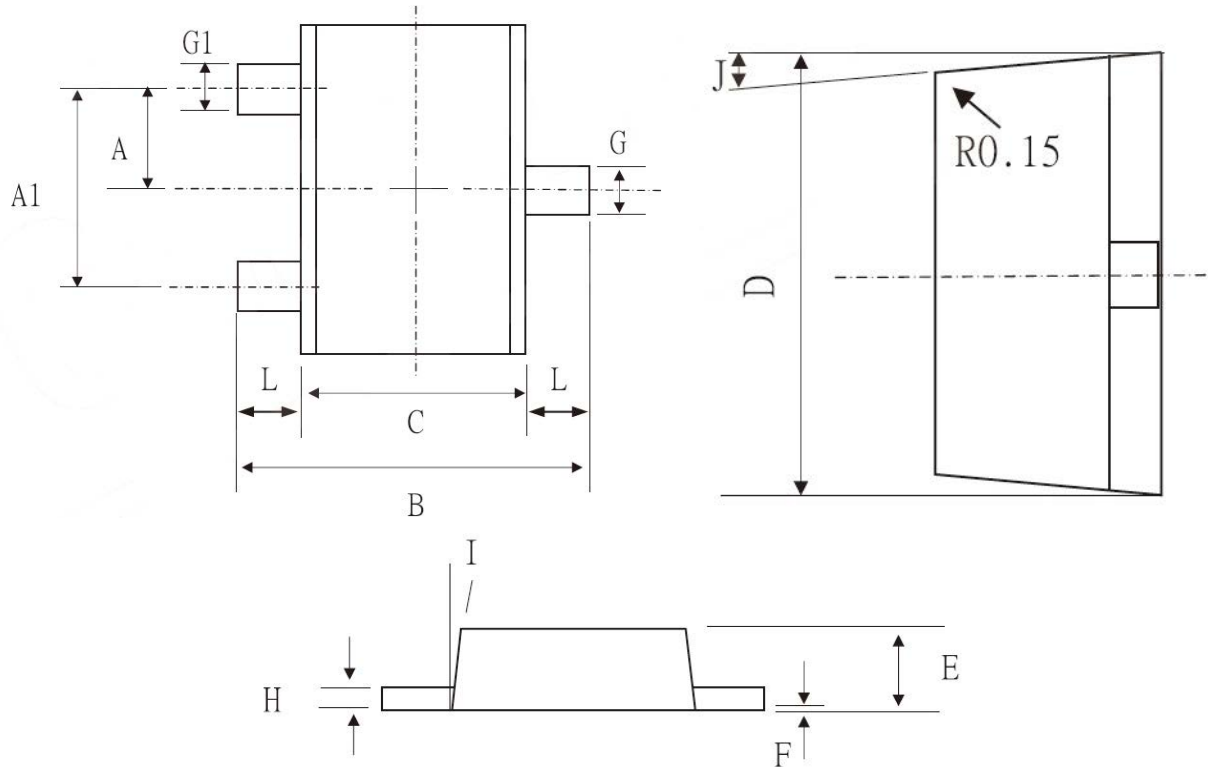


Fig.8 Gate Charge Waveform

PACKAGE OUTLINE & DIMENSIONS

YSE2320XUC

SOT-723 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	0.4BSC		0.016BSC	
A1	0.8BSC		0.031BSC	
B	1.250	1.150	0.049	0.045
C	0.850	0.750	0.033	0.030
D	1.250	1.150	0.049	0.045
E	0.390	0.370	0.015	0.015
F	0.050	0.000	0.002	0.000
G	0.270	0.220	0.011	0.009
G1	0.220	0.170	0.009	0.007
H	0.110	0.009	0.004	0.000
I	13°	9°	13°	9°
L	0.250	0.150	0.010	0.006
J	11°	7°	11°	7°